



Docket:  
90065.141001/17732.6317.003

#10  
Amelt  
B  
(NE)  
3-27-03  
ary  
4:2403  
ary

**IN THE UNITED STATES PATENT & TRADEMARK OFFICE**

|             |                                   |   |           |
|-------------|-----------------------------------|---|-----------|
| Applicant:  | Christopher B. Kocon, et al.      | ) | Examiner: |
|             |                                   | ) | Paul E.   |
| Serial No.: | 10/039,319                        | ) | Brock II  |
|             |                                   | ) |           |
| Filed:      | November 9, 2001                  | ) | Art Unit: |
|             |                                   | ) | 2815      |
| For:        | MOS GATED DEVICE HAVING A BURIED  | ) |           |
|             | GATE AND PROCESS FOR FORMING SAME | ) |           |

**RESPONSE TO OFFICE ACTION**

Assistant Commissioner for Patents  
Washington, DC 20231

Dear Sir:

RECEIVED  
MAR 19 2003  
TECHNOLOGY CENTER 2800

**Introduction**

This amendment cancels claims 24, 26, 32 and 33 without prejudice. It amends claim 21 to add a limitation that the depth of the source regions is substantially coplanar with the level of the conductive gate material. Claims 29 and 30 are amended to make them consistent with the elected species. New claims 40 and 41 define a process that excludes doped insulation layers and expressly requires ion implantation and diffusion for the source and body dopants.